

1N5614/US 1N5616/US 1N5618/US 1N5620/US 1N5622/US

TECHNICAL DATA DATA SHEET 116, REV. C

## HERMETIC AXIAL LEAD / MELF GENERAL PURPOSE RECTIFIER

DESCRIPTION: A 200/400/600/800/1000 VOLT, 1.0 AMP, AXIAL LEAD/SURFACE MOUNT 2000 NS GLASS RECTIFIER.

**MAXIMUM RATINGS** 

All ratings are at  $T_A = 25^{\circ}$ C unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) 1N5614 1N5616 1N5618 1N5620 1N5622		-	-	200 400 600 800 1000	Vdc
Average DC Output Current ( $I_o$ ) $T_c = 55$ °C $T_c = 100$ °C		-	-	1.0 0.75	Amps
Peak Single Cycle Surge Current (I <sub>fsm</sub> )	t <sub>p</sub> = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	30	Amps(pk)
Thermal Resistance ( <sub>0JL</sub> )	Junction to Lead d = 0.375"	-	-	36	°C/W
Thermal Resistance ( $\theta_{\text{JEC}}$ )	Junction to Endcap	-	-	13	°C/W
Operating and Storage Temp. (T <sub>op</sub> & T <sub>stg</sub> )	-	-65	-	+175	°C

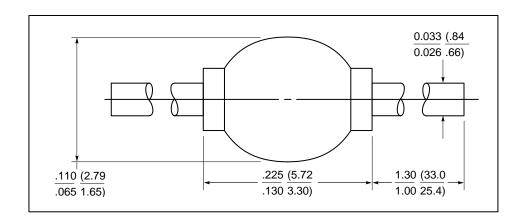
### **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum Forward Voltage (V <sub>f</sub> )	$I_F = 3.0A$ (300 µsec pulse, duty cycle < 2%)	-	-	1.3	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	T <sub>A</sub> = 25° C T <sub>A</sub> = 100° C	-	-	0.5 25	μAmps μAmps
Maximum Reverse Recovery Time	$I_F = 0.5A, I_R = 1.0A$ $I_{RR} = 0.25A$	-	-	2000	ns

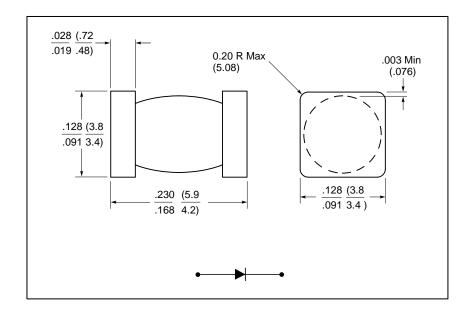
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#### **MECHANICAL DIMENSIONS: in inches / mm**



PKG. 102

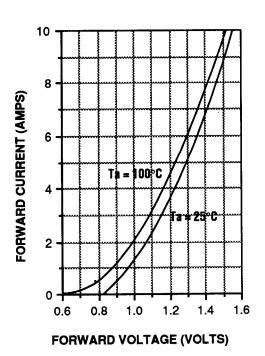


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# TYPICAL FORWARD VOLTAGE VERSUS FORWARD CURRENT (PULSED)



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